

ABSTRACT OF THE DISCLOSURE

A glass-sealed type semiconductor device has Dumet electrodes, a glass sealing member, and a semiconductor element tightly sealed in a cavity constituted by the Dumet electrodes and the glass sealing member. The semiconductor element is constituted by a Schottky barrier diode. External leads serving as external terminals of the semiconductor device are connected to the Dumet electrodes, respectively. The Dumet electrodes have core portions comprised of a nickel-iron alloy, copper layer formed on the outer peripheries of the core portions, and copper oxide layers formed on the outer surfaces of the copper layers, respectively. The ratios of the copper layers are 20 wt% or more each.